



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:
Stephen Keetai Park

Serial No.: 10/045,895

Filed: January 28, 2000


For: METHOD OF FABRICATING
COPPER-BASED SEMICONDUCTOR
DEVICES USING A SACRIFICIAL
DIELECTRIC LAYER

§
§
§ Examiner: Hsien-Ming Lee
§
§ Group Art Unit: 2823
§
§ Atty. Docket: 2000.029996/TT3586C
§
§
§

#6 2823
Pre-Amend B
D. Smalls-Logan
3/5/03
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PRELIMINARY AMENDMENT

BOX PATENT APPLICATION
Assistant Commissioner for Patents
Washington, D.C. 20231

CERTIFICATE OF MAILING UNDER C.F.R. § 1.8	
DATE OF DEPOSIT:	September 4, 2002
I hereby certify that this paper or fee is being deposited with the United States Postal Service with sufficient postage as "FIRST CLASS MAIL" addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231.	
 Signature	

Sir:

Please amend this application as follows:

AMENDMENTS

02/14/2003 SDAVIS 00000000 010365 10045895

01 FC:1202 In the claims:

Please amend claims 1, 5-7, 10-11, and 15-17 to read as follows:

1. A method of forming a copper interconnect, the method comprising:
- forming a first sacrificial dielectric layer above a structure layer and adjacent a contact;
- forming a second sacrificial dielectric layer above the first sacrificial dielectric layer and the contact;

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